

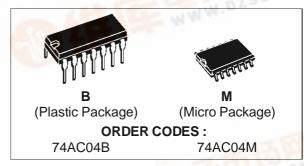
74AC04

# **HEX INVERTER**

- HIGH SPEED:  $t_{PD} = 4$  ns (TYP.) at  $V_{CC} = 5V$
- LOW POWER DISSIPATION:  $I_{CC} = 4 \mu A \text{ (MAX.)}$  at  $T_A = 25 \, ^{\circ}\text{C}$
- HIGH NOISE IMMUNITY: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (MIN.)
- 50Ω TRANSMISSION LINE DRIVING CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE: ||OH| = |OL = 24 mA (MIN)
- BALANCED PROPAGATION DELAYS:
  tplh ≅ tphl
- OPERATING VOLTAGE RANGE:
   V<sub>CC</sub> (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 04
- IMPROVED LATCH-UP IMMUNITY

#### DESCRIPTION

The AC04 is an advanced high-speed CMOS HEX INVERTER fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS

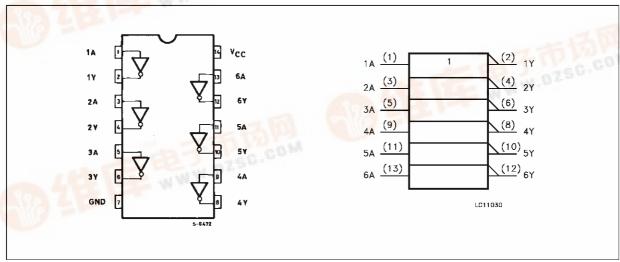


technology. It is ideal for low power applications mantaining high speed operation similar to equivalent Bipolar Schottky TTL.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

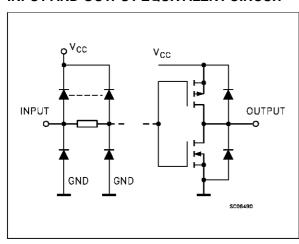
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

### PIN CONNECTION AND IEC LOGIC SYMBOLS





## INPUT AND OUTPUT EQUIVALENT CIRCUIT



### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Oututs
7	GND	Ground (0V)
14	Vcc	Positive Supply Voltage

#### **TRUTH TABLE**

Α	Υ
L	Н
Н	L

## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
lıĸ	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
lo	DC Output Current	± 50	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 300	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	2 to 6	V
Vı	Input Voltage	0 to Vcc	V
Vo	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature:	-40 to +85	°C
dt/dv	Input Rise and Fall Time V <sub>CC</sub> = 3.0, 4.5 or 5.5 V(note 1)	8	ns/V

<sup>1)</sup> V<sub>IN</sub> from 30% to 70% of V<sub>CC</sub>



### **DC SPECIFICATIONS**

Symbol	Parameter	Te	st Condi	tions			Value			Unit
		Vcc			T,	<sub>4</sub> = 25 °	,C	-40 to	85 °C	
		(V)			Min.	Тур.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input Voltage	3.0	Vo=	0.1 V or	2.1	1.5		2.1		
		4.5	V <sub>CC</sub> - 0.1 V	3.15	2.25		3.15		V	
		5.5		3.85	2.75		3.85			
VIL	Low Level Input Voltage	3.0		0.1 V or		1.5	0.9		0.9	
		4.5	Vcc	<sub>C</sub> - 0.1 V		2.25	1.35		1.35	V
		5.5				2.75	1.65		1.65	
Vон	High Level Output	3.0		I <sub>0</sub> =-50 μA	2.9	2.99		2.9		
	Voltage	4.5 V <sub>I</sub> <sup>(*)</sup> =	I <sub>O</sub> =-50 μA	4.4	4.49		4.4			
		5.5	V <sub>IH</sub> or	I <sub>O</sub> =-50 μA	5.4	5.49		5.4		V
		3.0	VIL	I <sub>O</sub> =-12 mA	2.56			2.46		
		4.5		I <sub>O</sub> =-24 mA	3.86			3.76		
		5.5		I <sub>O</sub> =-24 mA	4.86			4.76		
$V_{OL}$	Low Level Output	3.0		I <sub>O</sub> =50 μA		0.002	0.1		0.1	
	Voltage	4.5	V <sub>I</sub> <sup>(*)</sup> =	Io=50 μA		0.001	0.1		0.1	
		5.5	V <sub>IH</sub> or	I <sub>O</sub> =50 μA		0.001	0.1		0.1	V
		3.0	VIL	I <sub>O</sub> =12 mA			0.36		0.44	
		4.5		I <sub>O</sub> =24 mA			0.36		0.44	
		5.5		I <sub>O</sub> =24 mA			0.36		0.44	
l <sub>l</sub>	Input Leakage Current	5.5	V <sub>I</sub> = V	cc or GND			±0.1		±1	μΑ
I <sub>CC</sub>	Quiescent Supply Current	5.5	V <sub>I</sub> = V	<sub>CC</sub> or GND			4		40	μΑ
I <sub>OLD</sub>	Dynamic Output Current	5.5	V <sub>OLD</sub> =	1.65 V max					75	mA
Iohd	(note 1, 2)		Vohd =	3.85 V min					-75	mA

<sup>1)</sup> Maximum test duration 2ms, one output loaded at time

## AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}, R_L = 500 \Omega$ , Input $t_f = t_f = 3 \text{ ns}$ )

Symbol	Parameter	Test Condition		Value					Unit
		Vcc		T,	a = 25 °	C.	-40 to	85 °C	
		(V)		Min.	Тур.	Max.	Min.	Max.	
t <sub>PLH</sub>	Propagation Delay Time	3.3 <sup>(*)</sup>		1.5	5.0	9.0	1.0	10.0	nc
t <sub>PHL</sub>		5.0 <sup>(**)</sup>		1.5	4.0	7.0	1.0	8.0	ns

<sup>(\*)</sup> Voltage range is 3.3V ± 0.3V (\*\*) Voltage range is 5V ± 0.5V

## **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Tes	st Conditions	Value			Unit		
		Vcc	$T_A = 25  ^{\circ}\text{C}$ -40 t		T <sub>A</sub> = 25 °C		-40 to	85 °C	
		(V)		Min.	Тур.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance	5.0			4				pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	5.0			33				pF

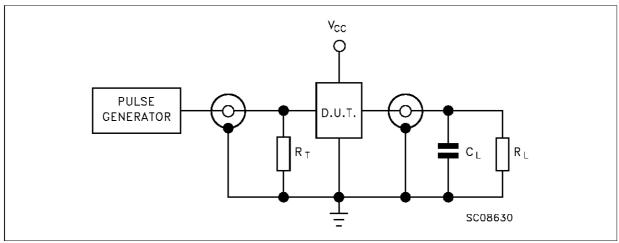
<sup>1)</sup>  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/n$  (per circuit)



<sup>2)</sup> Incident wave switching is guaranteed on transmission lines with impedances as low as 50  $\Omega$ .

<sup>(\*)</sup> All outputs loaded.

### **TEST CIRCUIT**

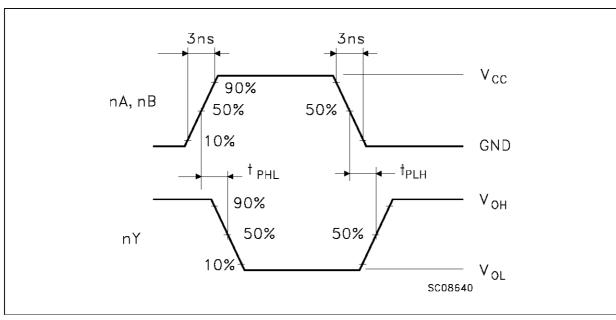


 $C_L = 50 \text{ pF}$  or equivalent (includes jig and probe capacitance)

 $R_L = R_1 = 500\Omega$  or equivalent

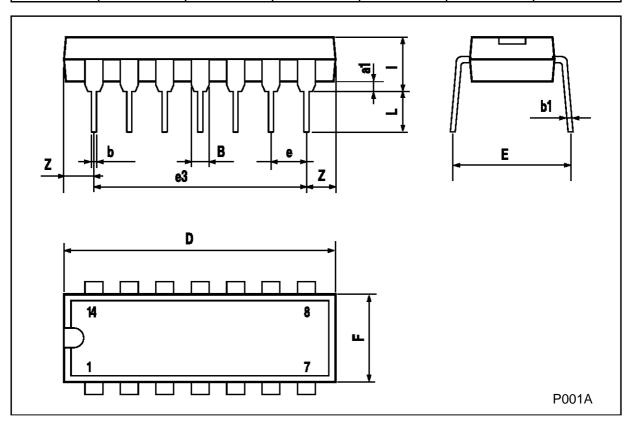
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

## WAVEFORM: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)



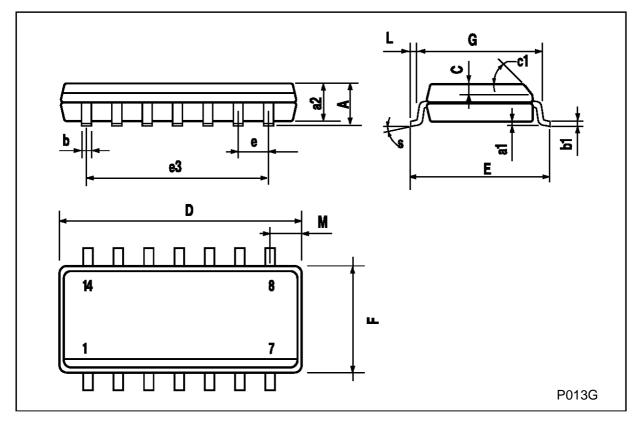
# **Plastic DIP14 MECHANICAL DATA**

DIM.		mm		inch				
Dini:	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	1.39		1.65	0.055		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		15.24			0.600			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z	1.27		2.54	0.050		0.100		



# **SO14 MECHANICAL DATA**

DIM.		mm			inch	
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45	(typ.)		
D	8.55		8.75	0.336		0.344
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.68			0.026
S		_	8 (1	max.)	_	



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